

# SMD Type 850nm Infrared Emitter

#### **Features**

- Small double-end package
- Viewing Angle at X axis (Note3) = ±55°
- High reliability
- Good spectral matching to Si photo detector
- RoHS compliance

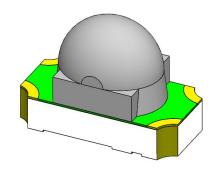
### **Applications**

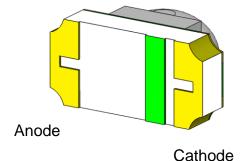
Infrared sensor

#### **Description**

The HIRP1608W11-B10 is a GaAlAs infrared LED housed in a miniature SMD package. The device has a peak wavelength of 850nm LED spectrally matched with phototransistor or photodiode.

### **Package Outline**





### **Schematic**

Cathode 
$$\longrightarrow$$
 Anode  $(-)$ 



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# Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
I <sub>F</sub>	Continuous Forward Current	70	mA	
I <sub>FP</sub>	Peak Forward Current	0.7	Α	1
V <sub>R</sub>	Reverse Voltage	5	V	
Topr	Operating Temperature	-40 ~ +85	°C	
T <sub>stg</sub>	Storage Temperature	-40 ~ +100	°C	
T <sub>sol</sub>	Soldering Temperature	260	°C	2
PD	Power Dissipation at(or below) 25°C Free Air Temperature	140	mW	

### Electro-Optical Characteristics TA = 25°C (unless otherwise specified)

#### **Optical Characteristics**

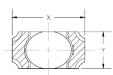
Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
le	Radiant Intensity	I <sub>F</sub> =20mA	2.5	4.5	8.0		
		I <sub>F</sub> =70mA	-	16	mW/sr	THVV/SI	
λр	Peak Wavelength	I <sub>F</sub> =20mA	-	850	-	nm	
Δλ	Spectral Bandwidth	I <sub>F</sub> =20mA	-	30	-	nm	
04/0	Angle of Half Intensity (X)	1 20m A	-	±55	-	-l	2
θ1/2	Angle of Half Intensity (Y)	I <sub>F</sub> =20mA	-	±37.5	-	deg	3

#### **Electrical Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
V Farward Voltage		I <sub>F</sub> =20mA	1.2	1.4	1.7	- V	
V <sub>F</sub> Forward Voltage	I <sub>F</sub> =70mA	1.3	1.6	2.0			
I <sub>R</sub>	Reverse Current	V <sub>R</sub> =5V	-	-	10	μΑ	

#### Notes:

- 1.  $I_{FP}$  Conditions--Pulse Width $\leq 100 \mu s$  and Duty $\leq 1\%$ .
- 2. Soldering time≦5 seconds
- 3. Test condition:

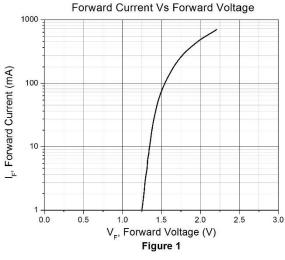


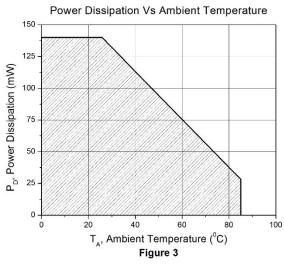


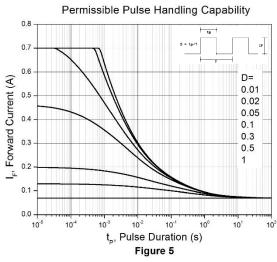


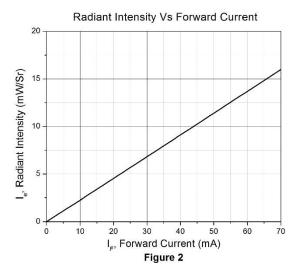
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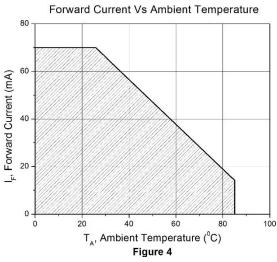
### **Typical Characteristic Curves**

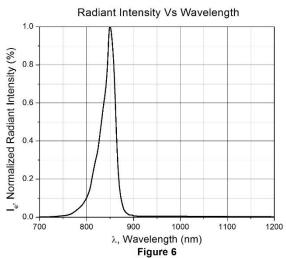












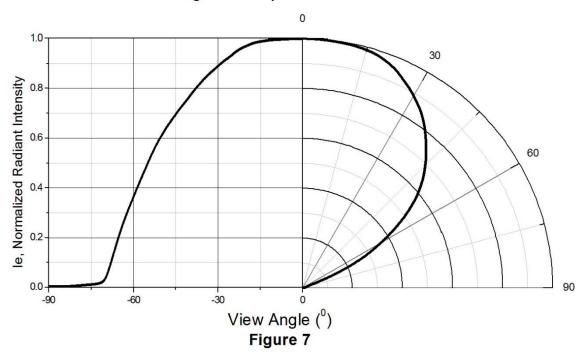




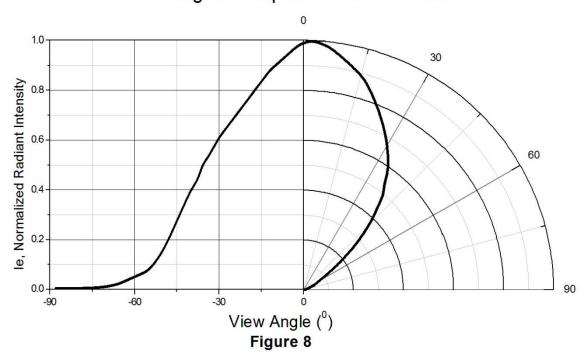
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# **Typical Characteristic Curves**

# Angular Displacement at X axis



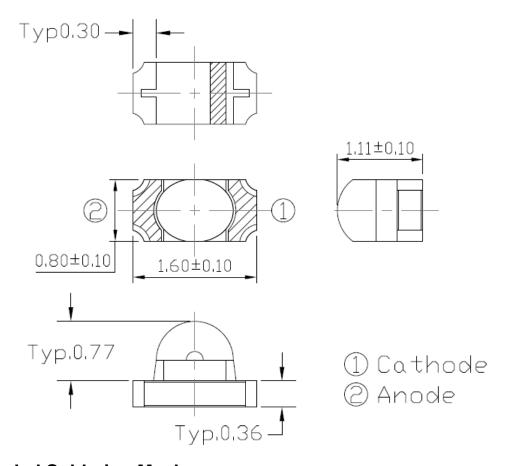
# Angular Displacement at Y axis



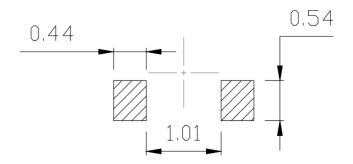


# SMD Type 850nm Infrared Emitter

### Package Dimension All dimensions are in mm, unless otherwise stated



### Recommended Soldering Mask All dimensions are in mm, unless otherwise stated



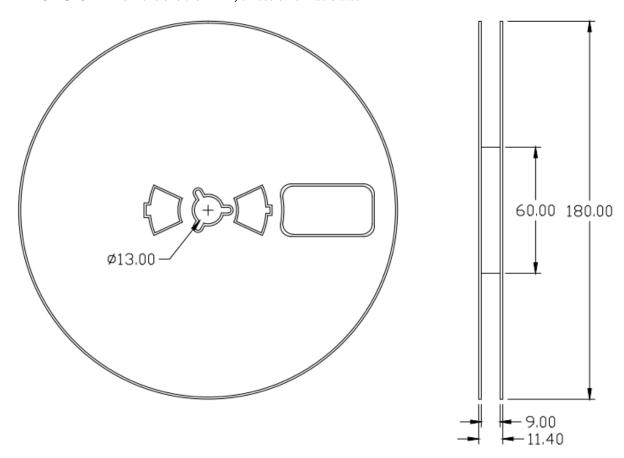
# **Ordering Information**

Part Number	Description	Quantity
HIRP1608W11-B10	Tape & Reel	3000 pcs

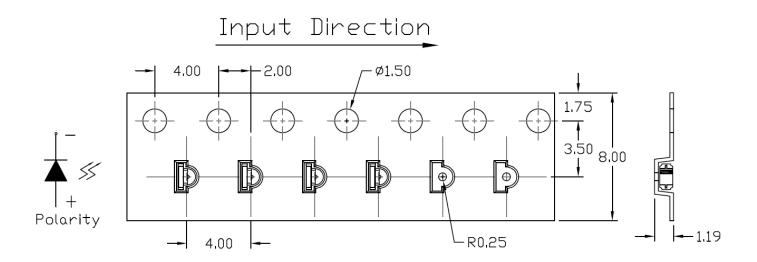


# SMD Type 850nm Infrared Emitter

### Reel Dimension All dimensions are in mm, unless otherwise stated



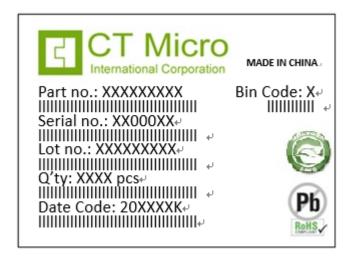
### Tape Dimension All dimensions are in mm, unless otherwise stated





### SMD Type 850nm Infrared Emitter

### **Label Form Specification**



Part no: CTM Production Number

Serial no: Production Number

Lot no: Lot number

Q'ty: Packing Quantity

Date Code: Manufacture Date

Bin Code: le Ranks

MADE IN CHINA: Production Place

#### **Storage Condition**

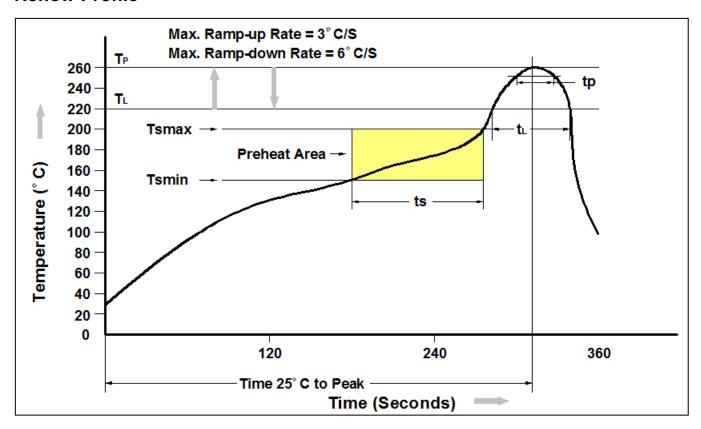
- 1. Do not open moisture proof bag before the products are ready to use.
- 2. The moisture barrier bag should be stored at 30°C and 90%R.H. max. before opening. Shelf life of non-opened bag is 12 months after the bag sealing date.
- 3. After opening the moisture barrier bag floor life is 168h at 30°C/60%RH. max. Unused LEDs should be resealed into moisture barrier bag. (Refer to J-STD-020 Standard)
- 4. If the moisture absorbent material has faded away or the LEDs have exceeded the storage time, baking treatment should be performed using the J-STD-033 Standard conditions.





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### **Reflow Profile**



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T∟)	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.